DATA SHEET

PMBF5484; PMBF5485; PMBF5486

N-channel field-effect transistors

Product specification
File under Discrete Semiconductors, SC07

April 1995

Philips
Semiconductors

PHILIPS

N-channel field-effect transistors

PMBF5484; PMBF5485; PMBF5486

FEATURES

- Low noise
- Interchangeability of drain and source connections
- High gain.

DESCRIPTION

N-channel, symmetrical, silicon junction FETs in a surface-mountable SOT23 envelope. Intended for use in VHF/UHF amplifiers, oscillators and mixers.

PINNING - SOT23

PIN	DESCRIPTION
1	source
2	drain
3	gate

MARKING CODES:

PMBF5484: p6B

PMBF5485: p6M

PMBF5486: p6H

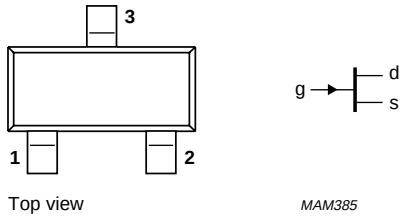


Fig.1 Simplified outline and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	25	V
I_{DSS}	drain current	V_{DS} = 15 V; V_{GS} = 0			
	PMBF5484		1	5	mA
	PMBF5485		4	10	mA
	PMBF5486		8	20	mA
P_{tot}	total power dissipation	up to T_{amb} = 25 °C	–	250	mW
$V_{GS(off)}$	gate-source cut-off voltage	V_{DS} = 15 V; I_D = 1 nA			
	PMBF5484		–0.3	–3	V
	PMBF5485		–0.5	–4	V
	PMBF5486		–2	–6	V
$\lvert Y_{fs} \rvert$	common source transfer admittance	V_{DS} = 15 V; V_{GS} = 0; f = 1 kHz			
	PMBF5484		3	6	mS
	PMBF5485		3.5	7	mS
	PMBF5486		4	8	mS

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	25	V
V_{GSO}	gate-source voltage		–	–25	V
V_{GDO}	gate-drain voltage		–	–25	V
I_G	DC forward gate current		–	10	mA
P_{tot}	total power dissipation	up to T_{amb} = 25 °C (note 1)	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

THERMAL RESISTANCE

SYMBOL	PARAMETER	THERMAL RESISTANCE
$R_{th\ j\text{-}a}$	from junction to ambient (note 1)	500 K/W

Note

1. Device mounted on an FR4 printed-circuit board.

STATIC CHARACTERISTICS

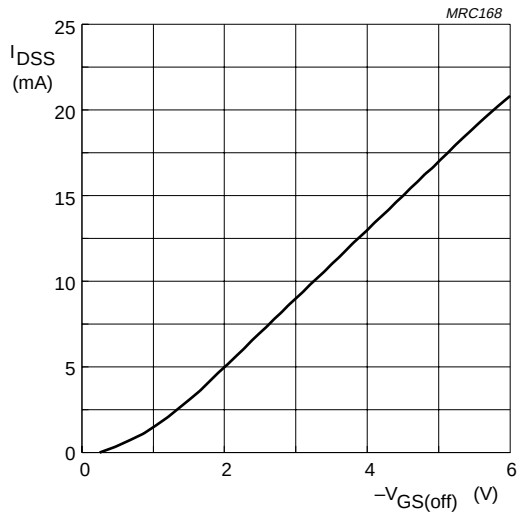
T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)GSS}$	gate-source breakdown voltage	V_{DS} = 0; I_G = –1 μA	–25	–	V
I_{DSS}	drain current	V_{DS} = 15 V; V_{GS} = 0			
	PMBF5484		1	5	mA
	PMBF5485		4	10	mA
	PMBF5486		8	20	mA
I_{GSS}	reverse gate leakage current	V_{DS} = 0; V_{GS} = –15 V	–	–1	nA
V_{GSS}	gate-source forward voltage	V_{DS} = 0; I_G = 1 mA	–	1	V
$V_{GS(off)}$	gate-source cut-off voltage	V_{DS} = 15 V; I_D = 1 nA			
	PMBF5484		–0.3	–3	V
	PMBF5485		–0.5	–4	V
	PMBF5486		–2	–6	V
$\lvert Y_{fs} \rvert$	common source transfer admittance	V_{DS} = 15 V; V_{GS} = 0			
	PMBF5484		3	6	mS
	PMBF5485		3.5	7	mS
	PMBF5486		4	8	mS
$\lvert Y_{os} \rvert$	common source output admittance	V_{DS} = 15 V; V_{GS} = 0			
	PMBF5484		–	50	μS
	PMBF5485		–	60	μS
	PMBF5486		–	75	μS

DYNAMIC CHARACTERISTICS

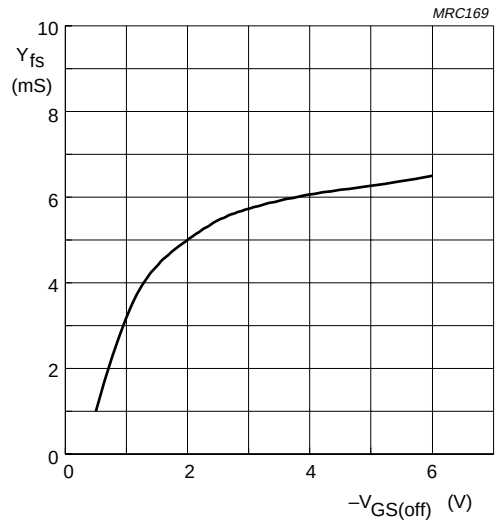
T_j = 25 °C; V_{DS} = 15 V; V_{GS} = 0

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
C_{is}	input capacitance	f = 1 MHz	–	–	5	pF
C_{os}	output capacitance	f = 1 MHz	–	–	2	pF
C_{rs}	feedback capacitance	f = 1 MHz	–	–	1	pF
g_{is}	common source input conductance					
	PMBF5484	f = 100 MHz	100	–	–	µS
	PMBF5485; PMBF5486	f = 400 MHz	–	–	1	mS
g_{fs}	common source transfer conductance					
	PMBF5484	f = 100 MHz	2.5	–	–	mS
	PMBF5485	f = 400 MHz	3	–	1	mS
	PMBF5486	f = 400 MHz	3.5	–	1	mS
g_{os}	common source output conductance					
	PMBF5484	f = 100 MHz	–	–	75	µS
	PMBF5485; PMBF5486	f = 400 MHz	–	–	100	µS
V_n	equivalent input noise voltage	f = 100 Hz	–	5	–	nV/√Hz



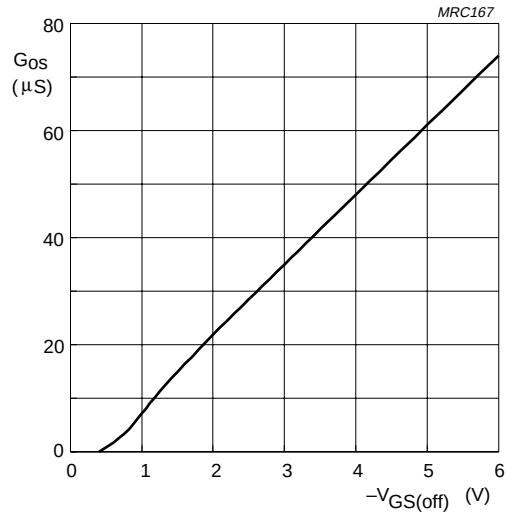
V_{DS} = 15 V; T_j = 25 °C; typical values.

Fig.2 Drain current as a function of gate-source cut-off voltage.



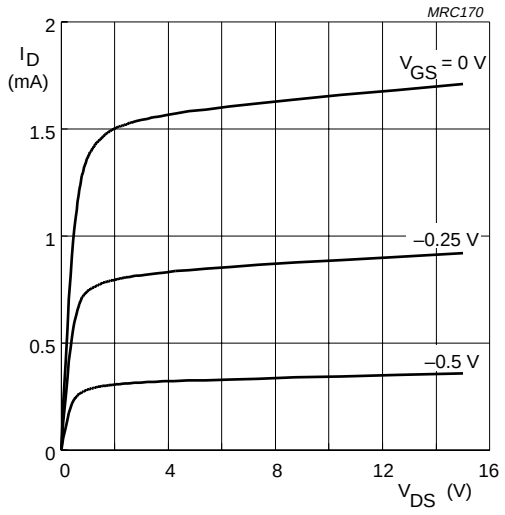
V_{DS} = 15 V; T_j = 25 °C; typical values.

Fig.3 Common source transfer admittance as a function of gate-source cut-off voltage.



V_{DS} = 15 V; T_j = 25 °C; typical values.

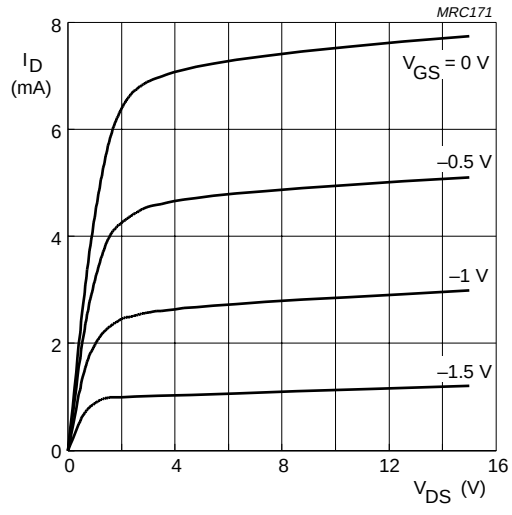
Fig.4 Common source output conductance as a function of gate-source cut-off voltage.



PMBF5484

T_j = 25 °C.

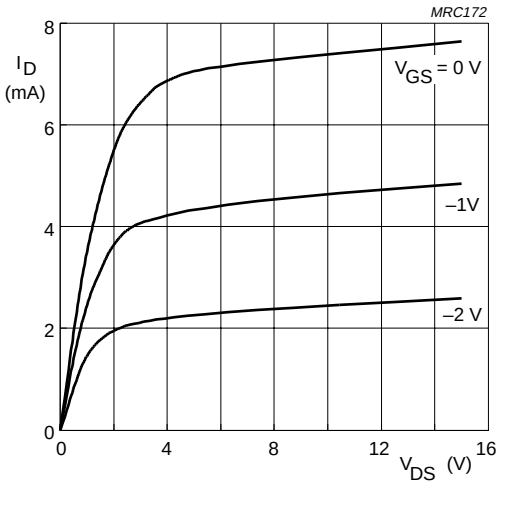
Fig.5 Typical output characteristics.



PMBF5485

T_j = 25 °C.

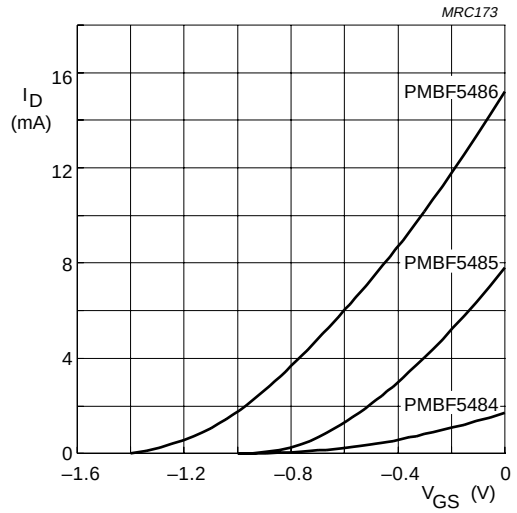
Fig.6 Typical output characteristics.



PMBF5486

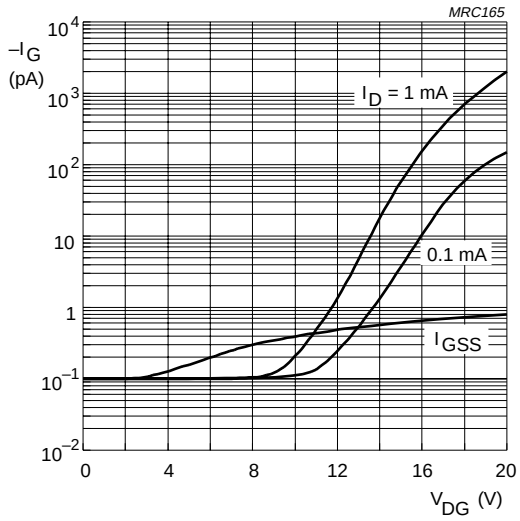
T_j = 25 °C.

Fig.7 Typical output characteristics.



V_{DS} = 15 V; T_j = 25 °C.

Fig.8 Typical input characteristics.



T_j = 25 °C.

Fig.9 Gate current as a function of drain-gate voltage, typical values.

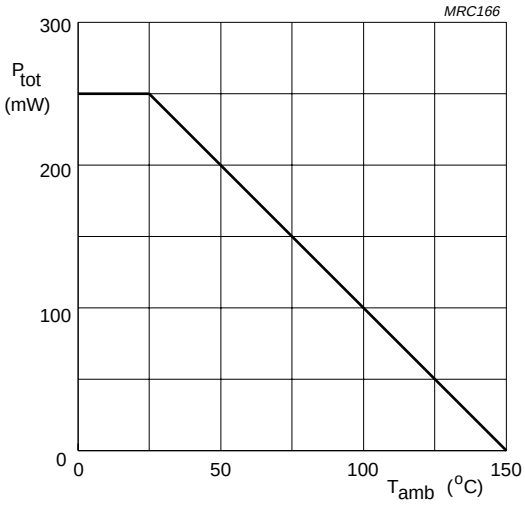
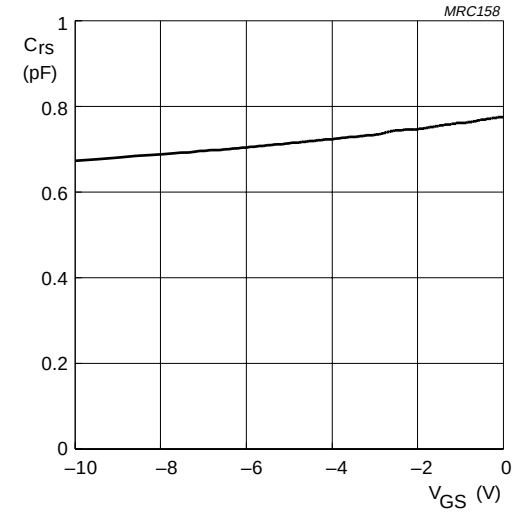
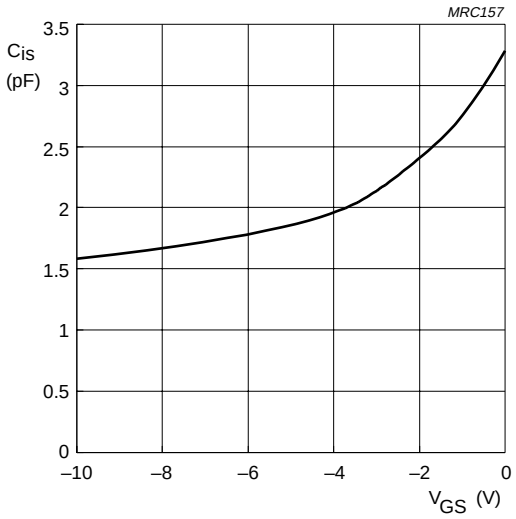


Fig.10 Power derating curve.



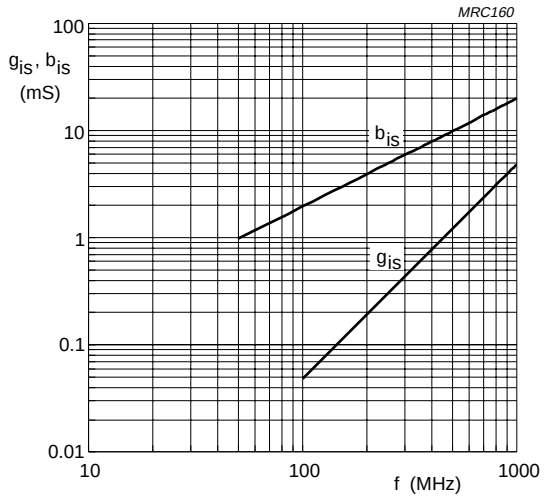
V_{DS} = 15 V; T_j = 25 °C.

Fig.11 Typical feedback capacitance.



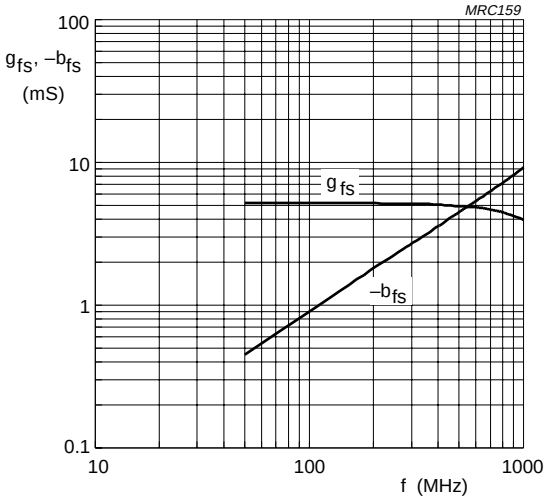
V_{DS} = 15 V; T_j = 25 °C.

Fig.12 Typical input capacitance.



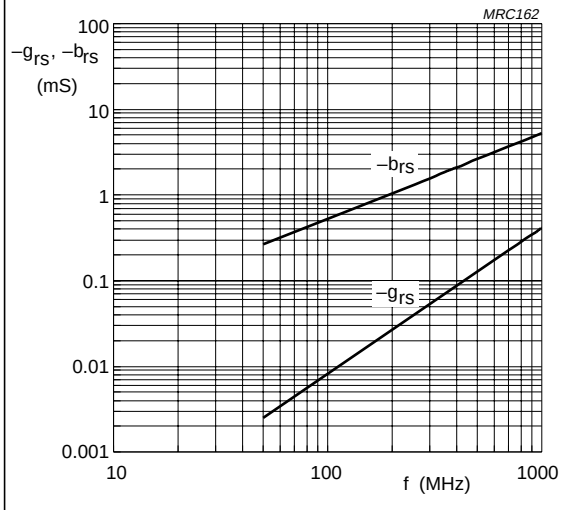
V_{DS} = 15 V; V_{GS} = 0; T_{amb} = 25 °C; typical values.

Fig.13 Common source input conductance.



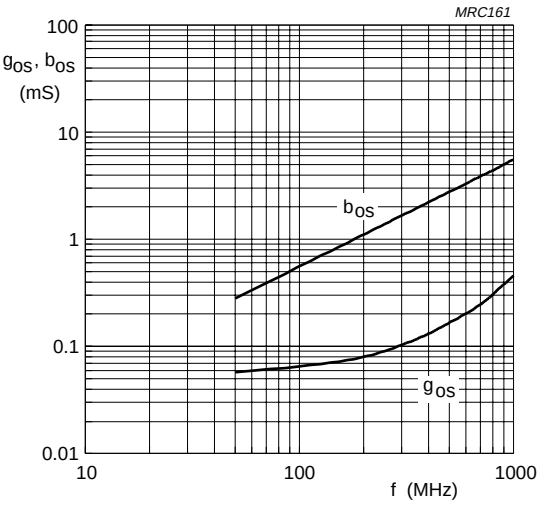
V_{DS} = 15 V; V_{GS} = 0; T_{amb} = 25 °C; typical values.

Fig.14 Common source transfer conductance.



V_{DS} = 15 V; V_{GS} = 0; T_{amb} = 25 °C; typical values.

Fig.15 Common source feedback conductance.

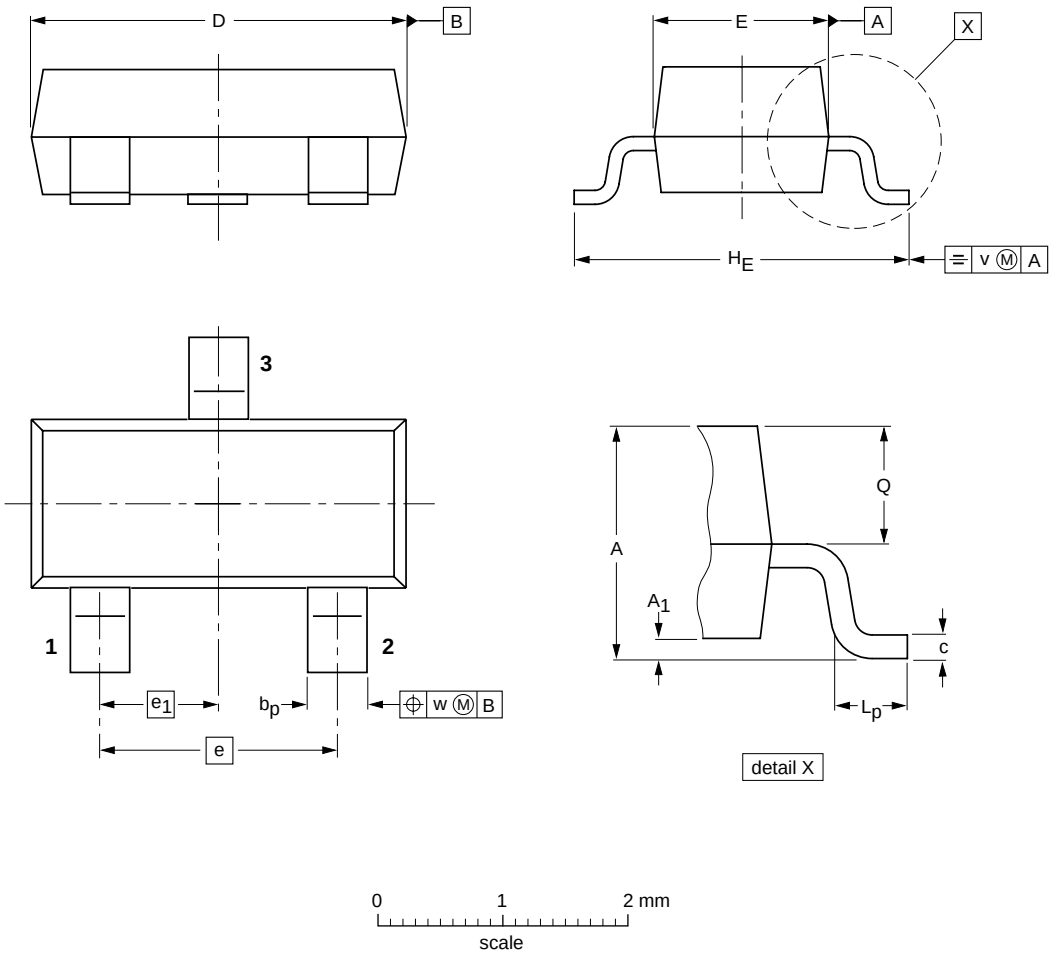


V_{DS} = 15 V; V_{GS} = 0; T_{amb} = 25 °C; typical values.

Fig.16 Common source output conductance.

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT23**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max.	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23						97-02-28

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Short-form specification	The data in this specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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